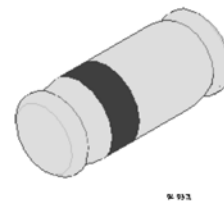


Switching Diode (FHLL4148)

Description

- The **FHLL4148** is designed for high-speed switching application in hybrid thick-and-thin-film circuits.
- Small surface mouting type.(**LL-34**)



ABSOLUTE MAXIMUM RATINGS 最大额定值 ($T_A=25^{\circ}\text{C}$)

RATING 额定值	Symbol	Value	Unit
Reverse Voltage 反向电压	V_R	75	V
Repetitive Peak Reverse Voltage 反向峰值电压	V_{RM}	100	V
Rectifier Current (average) 整流电流 Half Wave Rectification with Resist. Load At $T_A=25^{\circ}\text{C}$ and $f \geq 50\text{Hz}$	I_O	150	mA
Surge Forward Current 正向浪涌电流 at $t < 1 \mu\text{s}$ and $T_A=25^{\circ}\text{C}$	I_{FSM}	2	A
Power Dissipation 分散功率 at $T_A=25^{\circ}\text{C}$	P_{TOT}	500	mW
Junction Temperature 结温度	T_J	200	$^{\circ}\text{C}$
Storage Temperature Range 存储温度	T_S	-65 to +200	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS 电特性($T_A=25^{\circ}\text{C}$)

Characteristic 特性参数	Symbol	Min	Typ	Max	Unit
Forward Voltage 正向电压 At $I_F=10\text{mA}$	V_F			1	V
Leakage current 漏电流 At $V_R=20\text{v}$	I_R	-	-	25	nA
At $V_R=75\text{v}$	I_R	-	-	5	μA
At $V_R=20\text{v}, T_J=150^{\circ}\text{C}$	I_R	-	-	50	μA
Reverse Breakage Voltage 反向击穿电压 $I_{BR}=5 \mu\text{A dc}$ $I_{BR}=100 \mu\text{A dc}$	$V_{(BR)R}$	75 100	-	-	V
Capacitance 电容 At ($V_R=0, f=1.0\text{MHz}$)	C_{tot}	-	-	4	pF
Reverse Recovery Time 反向恢复时间 From $I_F=10\text{mA}$ to $I_R=1\text{mA}, V_R=6\text{V}, R=100\Omega$	T_{rr}	-	-	4	ns
Thermal Resistance Junction to ambient air 热阻	$R_{\theta JA}$	-	-	0.35	$^{\circ}\text{C}/\text{mW}$
Rectification Efficiency 整流功率 At $f=100\text{MHz}, V_{RF}=2\text{V}$	η_r	0.45	-	-	-

Notes: (1)Valid provided that electrodes are kept at ambient temperature.

(2)Device mouted on **FR4** printed-circuit board.

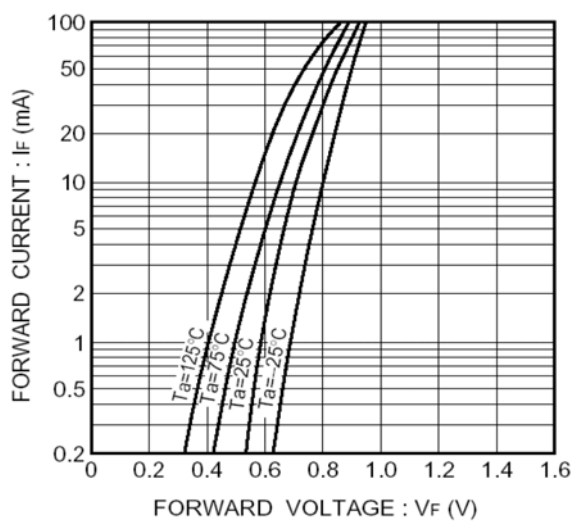


Fig.1 Forward characteristics

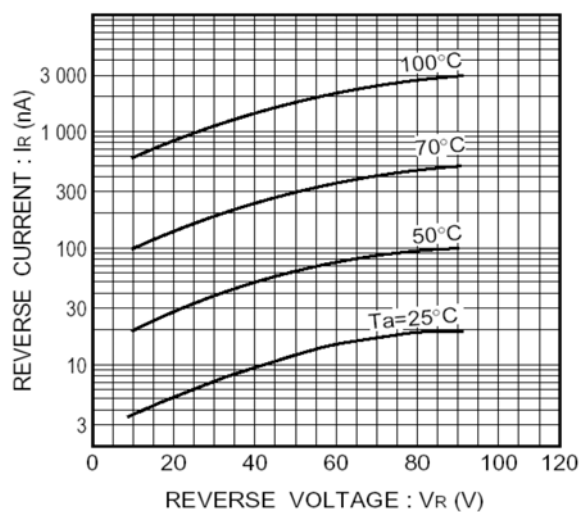


Fig.2 Reverse characteristics

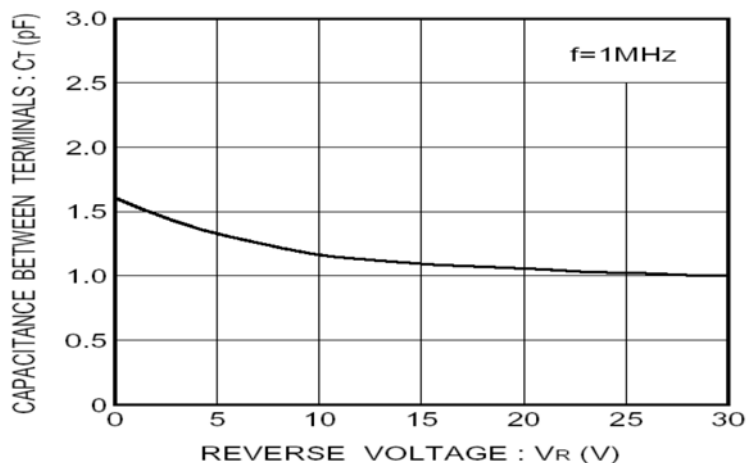


Fig.3 Capacitance between terminals characteristics

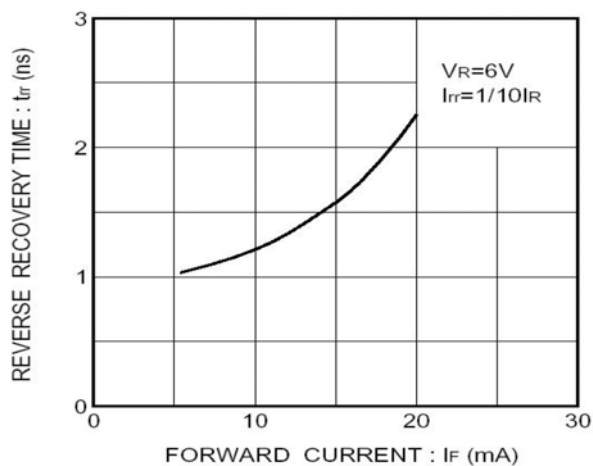


Fig.4 Reverse recovery time characteristics

Dimensions 封装外形尺寸

Dimensions in mm

